

# TFN1768

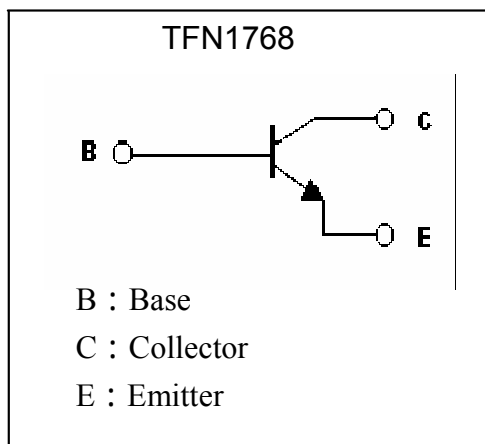
## Description

The TFN1768 is designed for use in driver and output stages of AF amplifier and general purpose application.

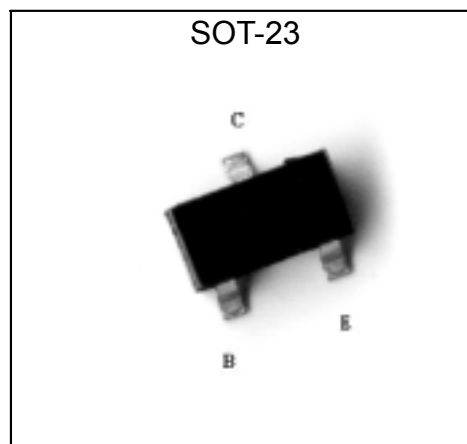
## Features

- Low collector saturation voltage
- High breakdown voltage,  $V_{CEO}=80V$  (min.)
- High collector current,  $I_{C(max)}=1A$  (DC)
- Pb-free package

## Symbol



## Outline



## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	80	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current (DC)	$I_C$	1	A
Collector Current (Pulse)	$I_{CP}$	2 (Note)	A
Power Dissipation	$P_D$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Operating Junction and Storage Temperature Range	$T_j ; T_{stg}$	-55~+150	°C

Note : Pulse test,  $P_w \leq 10ms$ , Duty  $\leq 50\%$ .



Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	100	-	-	V	I <sub>C</sub> =50μA
BV <sub>CEO</sub>	80	-	-	V	I <sub>C</sub> =1mA
BV <sub>EBO</sub>	5	-	-	V	I <sub>E</sub> =50μA
I <sub>CBO</sub>	-	-	1	μA	V <sub>CB</sub> =80V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	1	μA	V <sub>EB</sub> =4V, I <sub>C</sub> =0
*V <sub>CE(SAT)</sub>	-	0.15	0.4	V	I <sub>C</sub> =500mA, I <sub>B</sub> =20mA
*h <sub>FE</sub>	120	-	560	-	V <sub>CE</sub> =3V, I <sub>C</sub> =100mA
f <sub>T</sub>	-	100	-	MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA, f=100MHz
C <sub>ob</sub>	-	20	-	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz

\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of hFE

Rank	Q	R	S
Range	120~270	180~390	270~560

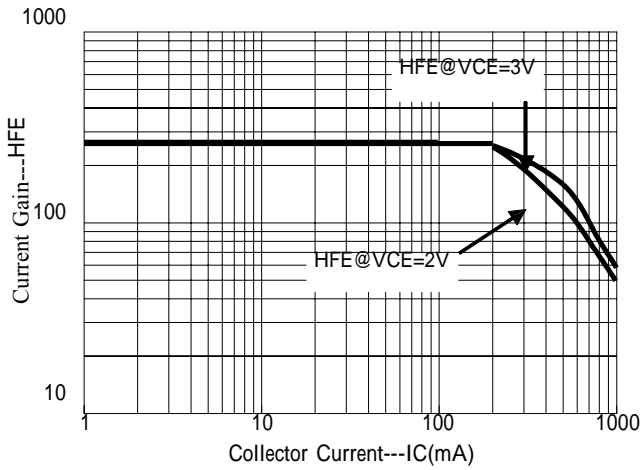
Ordering Information

Device	Package	Shipping	Marking
TFN1768	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	AJ

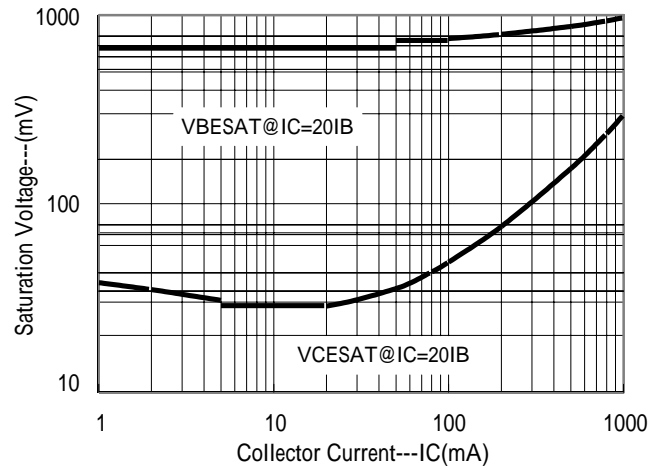


Typical Characteristics

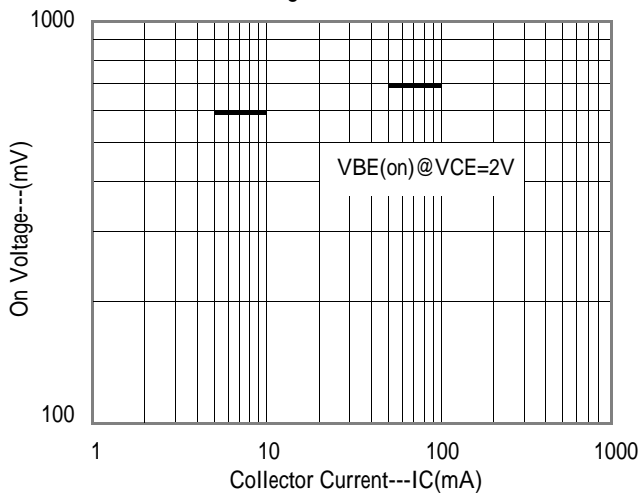
Current Gain vs Collector Current



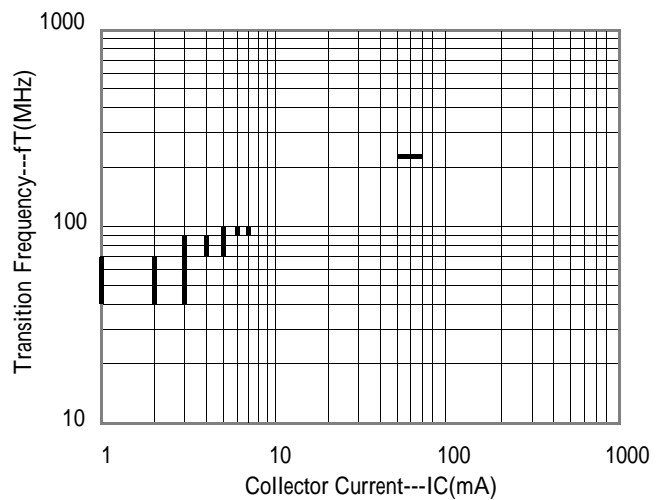
Saturation Voltage vs Collector Current



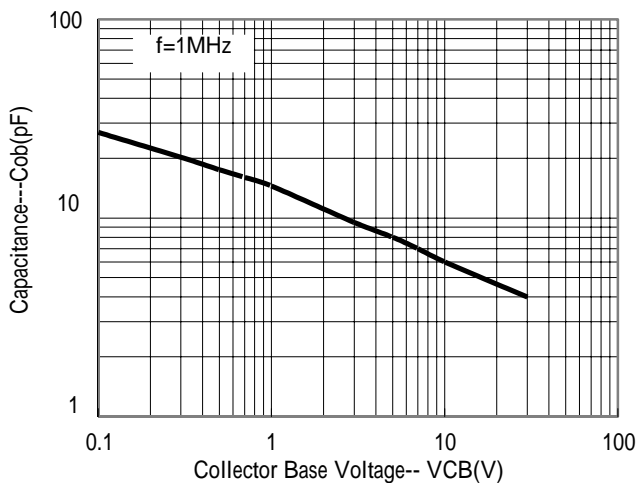
On Voltage vs Collector Current



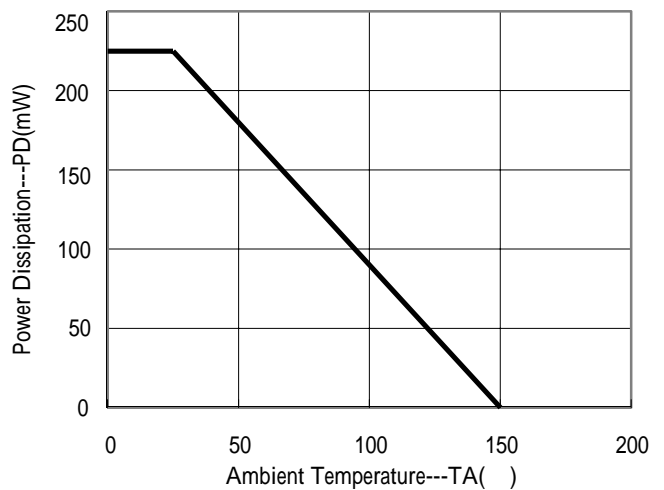
Transition Frequency vs Collector Current



Capacitance Characteristics

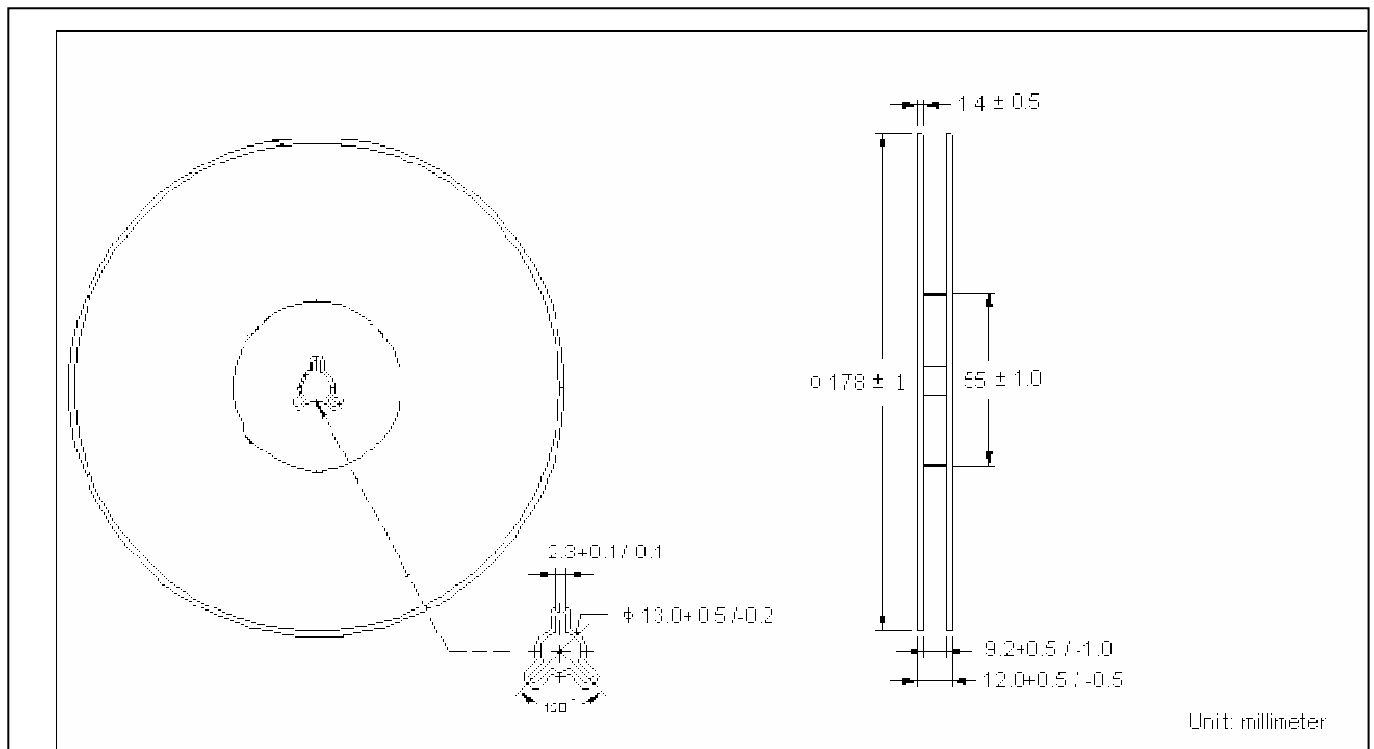


Power Derating Curve

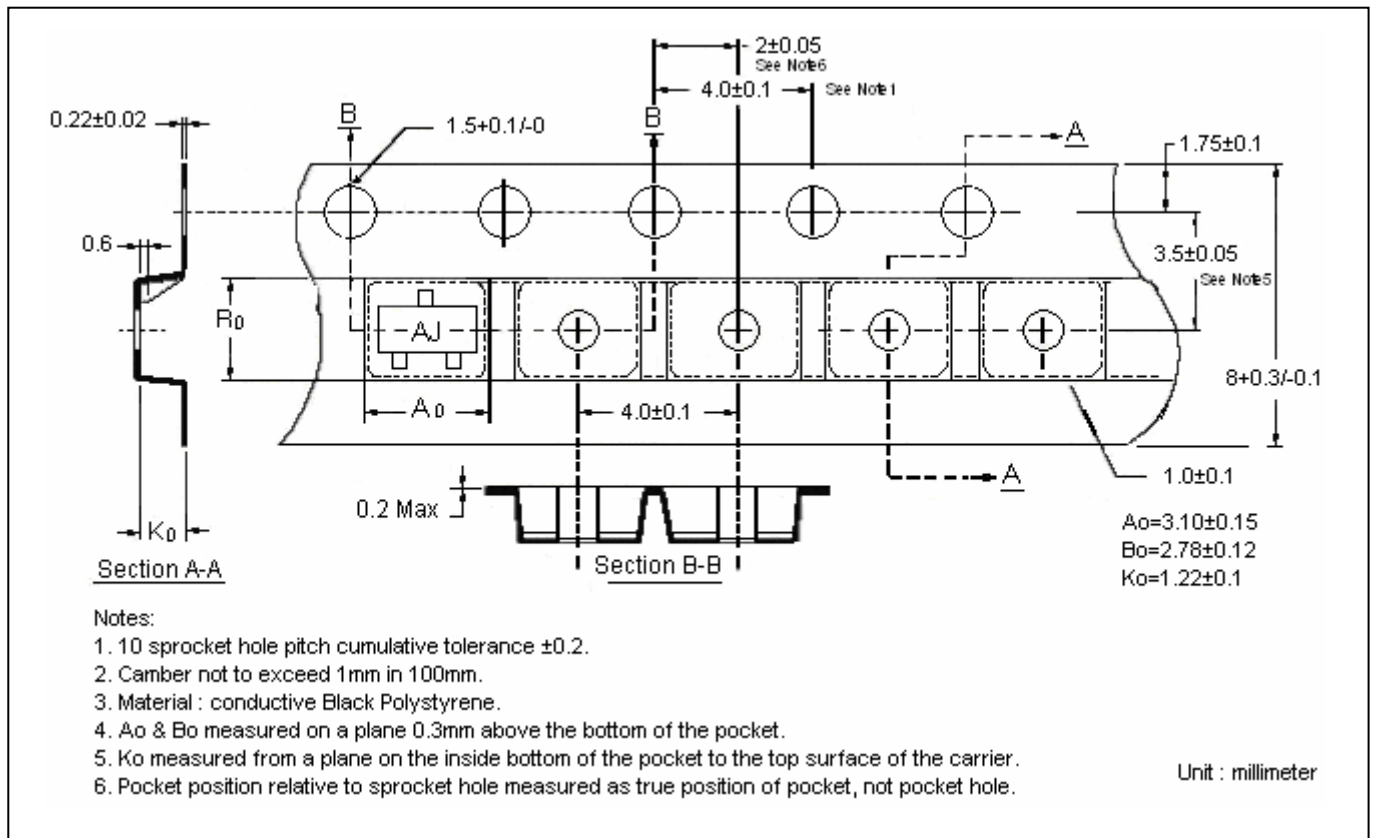




### Reel Dimension



### Carrier Tape Dimension

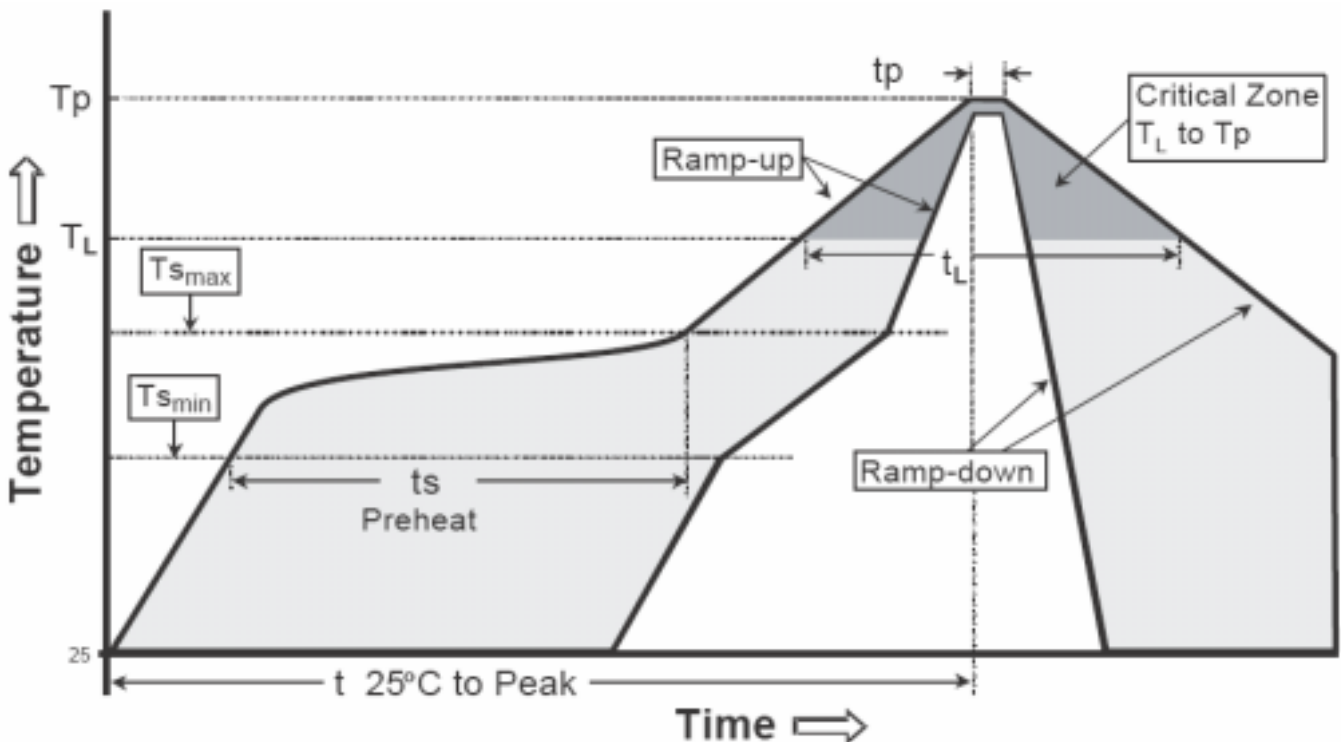




**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tl)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.



SOT-23 Dimension

Product Code

Date Code: Year+Month  
 Year: 7 2007, 8 2008  
 Month: 1 1, 2 2,  
 9 9, A 10, B 11, C 12

Marking:  
  
 3-Lead SOT-23 Plastic Surface Mounted Package

Style : Pin 1.Base 2.Emitter 3.Collector

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes : 1.Controlling dimension : millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local Tin Far sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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